

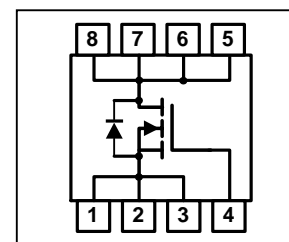
## Automotive MOSFET

### OptiMOS™-5 Power-Transistor



#### Features

- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Normal Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested



#### Potential applications

General automotive applications.

#### Product validation

Qualified for automotive applications. Product validation according to AEC-Q101.

#### Product Summary

$V_{DS}$	60	V
$R_{DS(on)}$	1.12	mΩ
$I_D$ (chip limited)	310	A

Type	Package	Marking
IAUC120N06S5N011	PG-TDSON-8-53	5N06N011



## Table of Contents

Description .....	1
Maximum ratings .....	3
Thermal characteristics .....	4
Electrical characteristics .....	4
Electrical characteristics diagrams .....	6
Package outline & footprint .....	10
Revision history .....	11
Disclaimer .....	12

## Maximum ratings

at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$V_{GS}=10\text{ V}$ , Chip limitation <sup>1,2)</sup>	310	A
		$V_{GS}=10\text{V}$ , DC current <sup>3)</sup>	120	
		$T_a=85\text{ °C}$ , $V_{GS}=10\text{ V}$ , $R_{thJA}$ on 2s2p <sup>2,4)</sup>	39	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$ , $t_p=100\text{ }\mu\text{s}$	1000	
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	$I_D=60\text{ A}$	485	mJ
Avalanche current, single pulse	$I_{AS}$	–	120	A
Gate source voltage	$V_{GS}$	–	$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	188	W
Operating and storage temperature	$T_j, T_{stg}$	–	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	–	–	55/175/56	

## Thermal characteristics<sup>2)</sup>

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	–	–	–	0.80	K/W
Thermal resistance, junction - ambient <sup>4)</sup>	$R_{thJA}$	–	–	26	–	

## Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$	60	–	–	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=130\text{ }\mu\text{A}$	2.2	2.8	3.4	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=60\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$	–	–	1	$\mu\text{A}$
		$V_{DS}=60\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=100\text{ °C}^{2)}$	–	–	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	–	–	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=7\text{ V}$ , $I_D=30\text{ A}$	–	1.12	1.30	m $\Omega$
		$V_{GS}=10\text{ V}$ , $I_D=60\text{ A}$	–	0.97	1.12	
Gate resistance <sup>2)</sup>	$R_G$	–	–	2.0	–	$\Omega$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=30\text{ V}, f=1\text{ MHz}$	-	7555	9822	pF
Output capacitance	$C_{oss}$		-	1622	2109	
Reverse transfer capacitance	$C_{rss}$		-	75	112	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30\text{ V}, V_{GS}=10\text{ V}, I_D=60\text{ A}, R_G=3.5\ \Omega$	-	19	-	ns
Rise time	$t_r$		-	10	-	
Turn-off delay time	$t_{d(off)}$		-	38	-	
Fall time	$t_f$		-	24	-	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=30\text{ V}, I_D=60\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	-	32	42	nC
Gate to drain charge	$Q_{gd}$		-	19	29	
Gate charge total	$Q_g$		-	105	137	
Gate plateau voltage	$V_{plateau}$		-	4.24	-	V

**Reverse Diode**

Diode continuous forward current <sup>2)</sup>	$I_S$	$T_C=25\text{ °C}$	-	-	120	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	$T_C=25\text{ °C}, t_p=100\ \mu\text{s}$	-	-	1000	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=60\text{ A}, T_j=25\text{ °C}$	-	0.8	1.1	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=30\text{ V}, I_F=50\text{ A}, di_f/dt=100\text{ A}/\mu\text{s}$	-	63	-	ns
Reverse recovery charge <sup>2)</sup>	$Q_{rr}$		-	75	-	

<sup>1)</sup> Practically the current is limited by the overall system design including the customer-specific PCB.

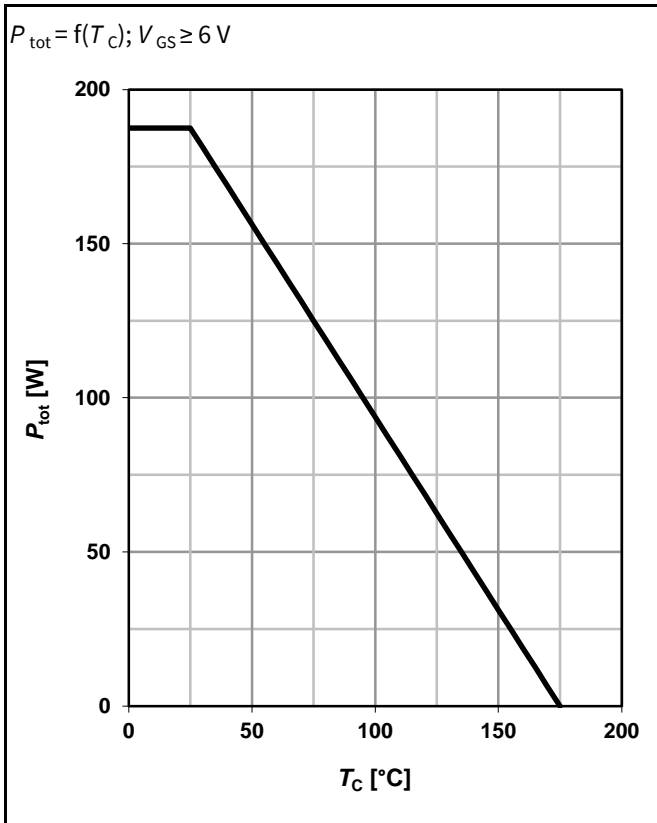
<sup>2)</sup> The parameter is not subject to production testing – specified by design.

<sup>3)</sup> Current is limited by package.

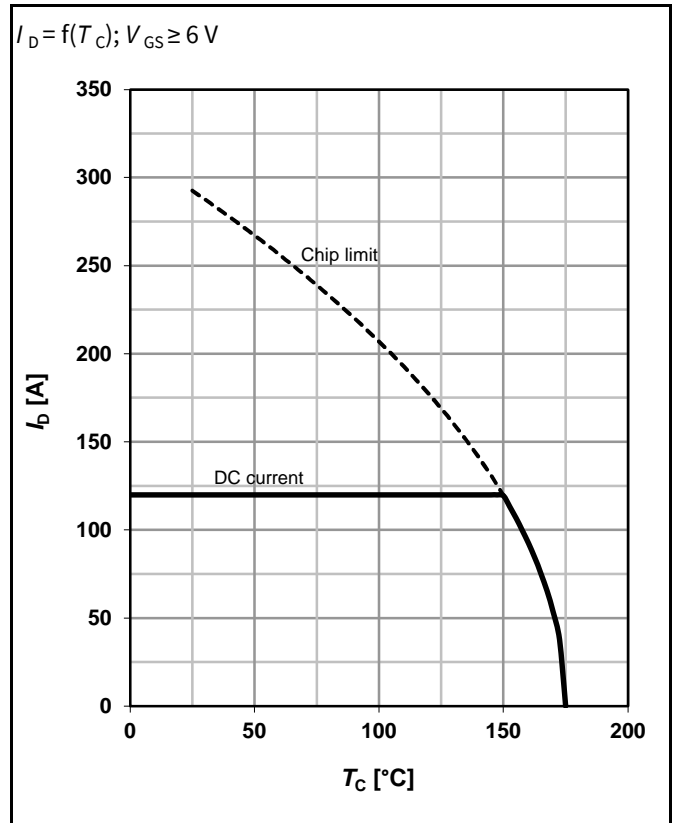
<sup>4)</sup> Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

### Electrical characteristics diagrams

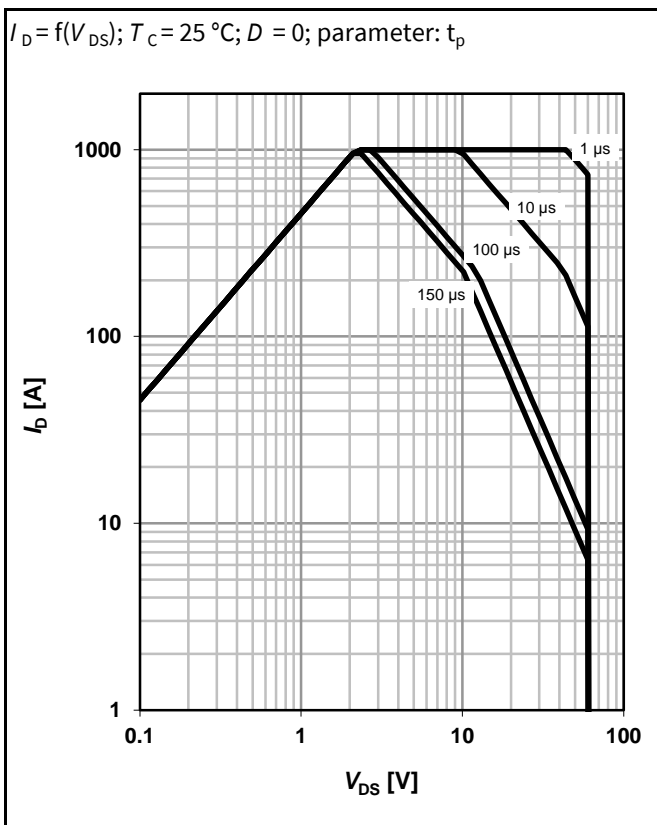
#### 1 Power dissipation



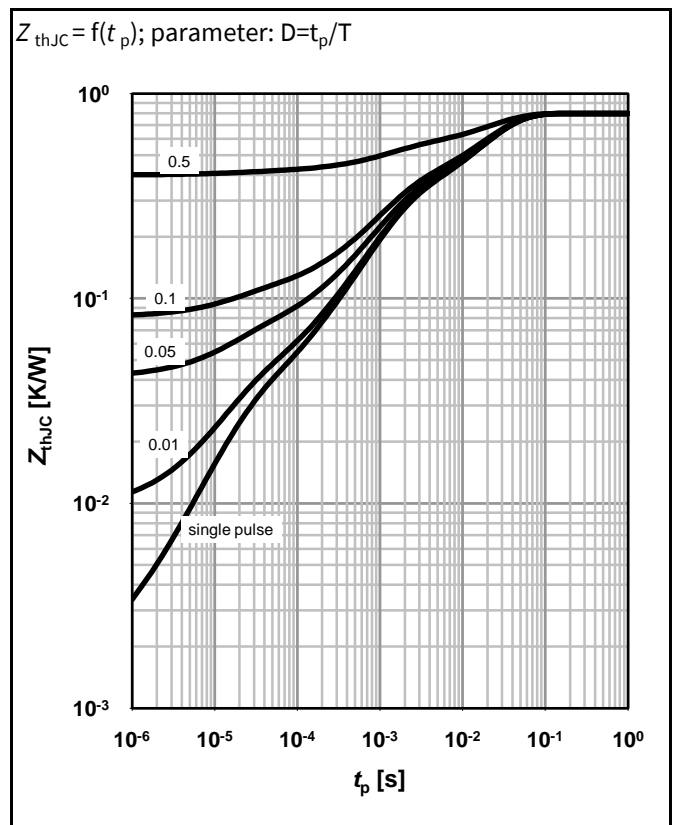
#### 2 Drain current



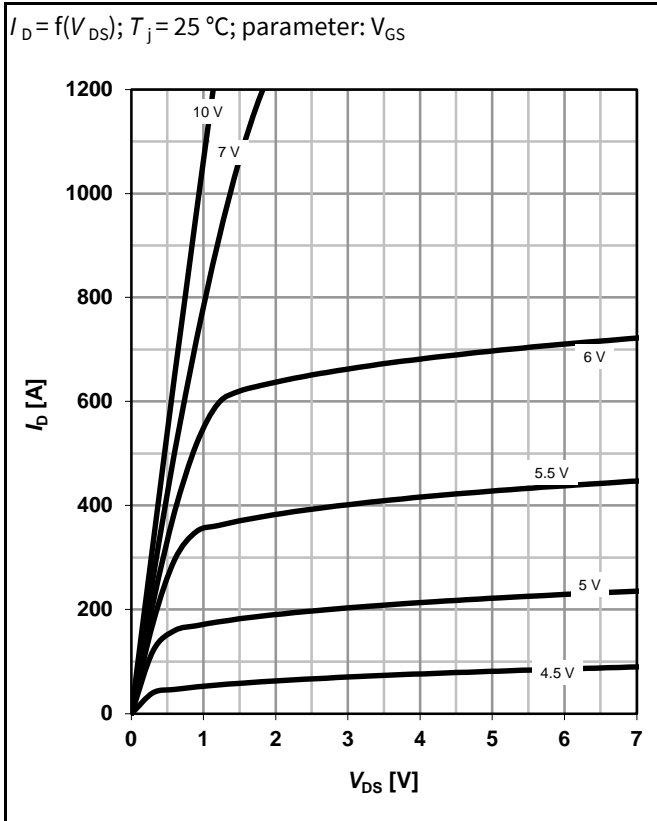
#### 3 Safe operating area



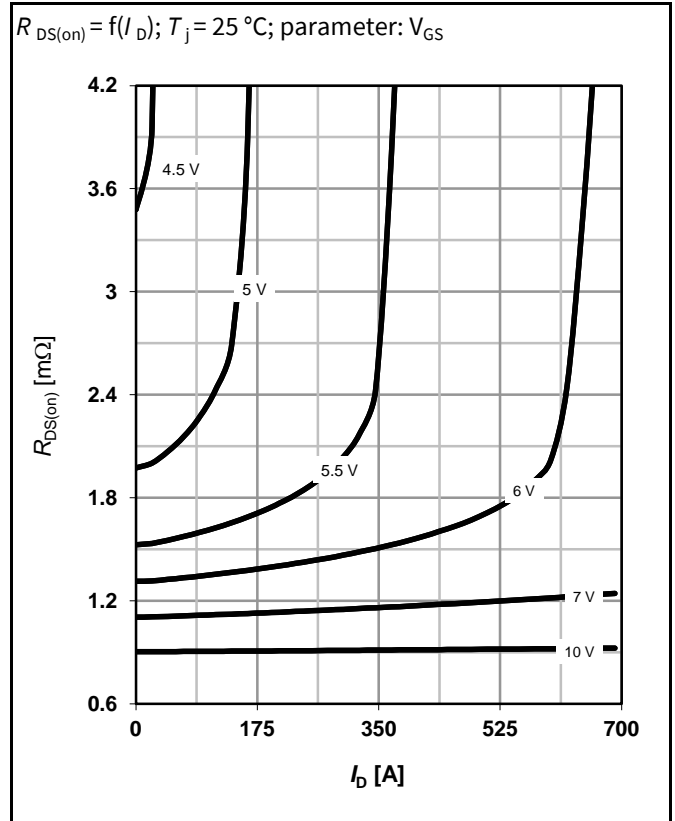
#### 4 Max. transient thermal impedance



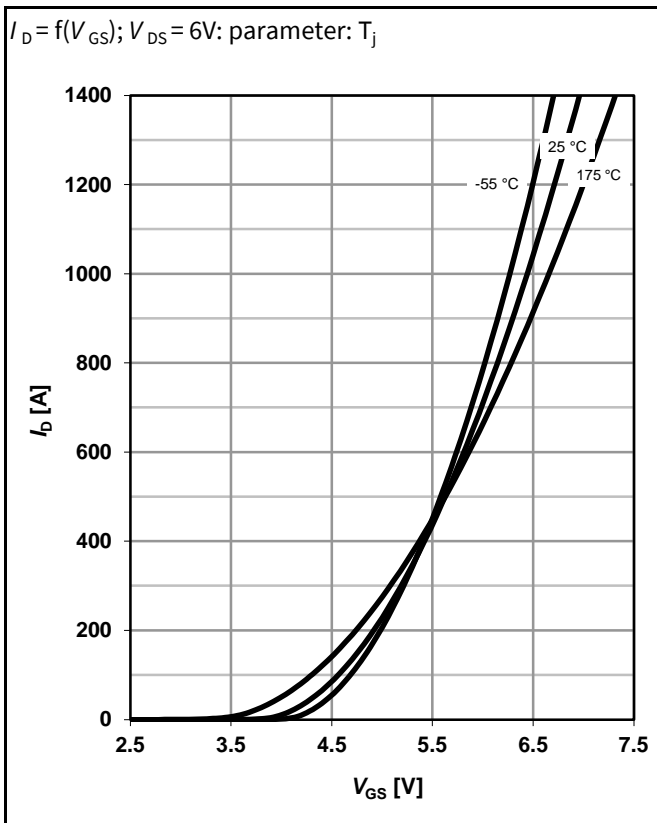
5 Typ. output characteristics



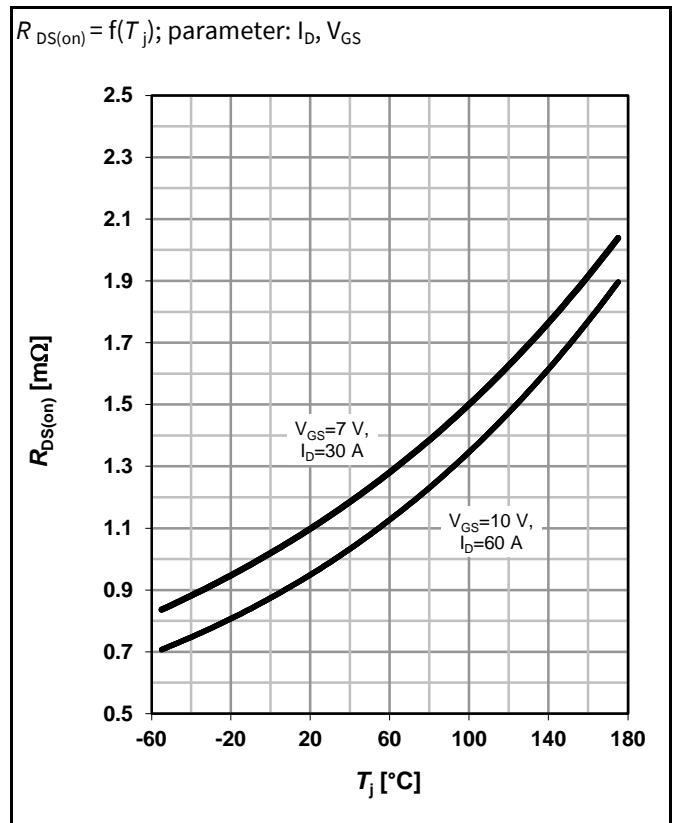
6 Typ. drain-source on-state resistance



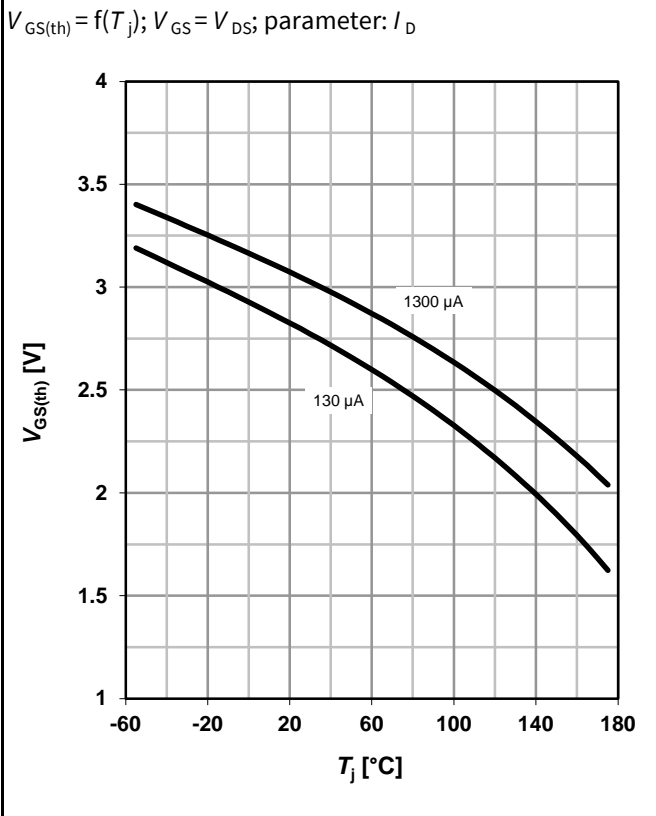
7 Typ. transfer characteristics



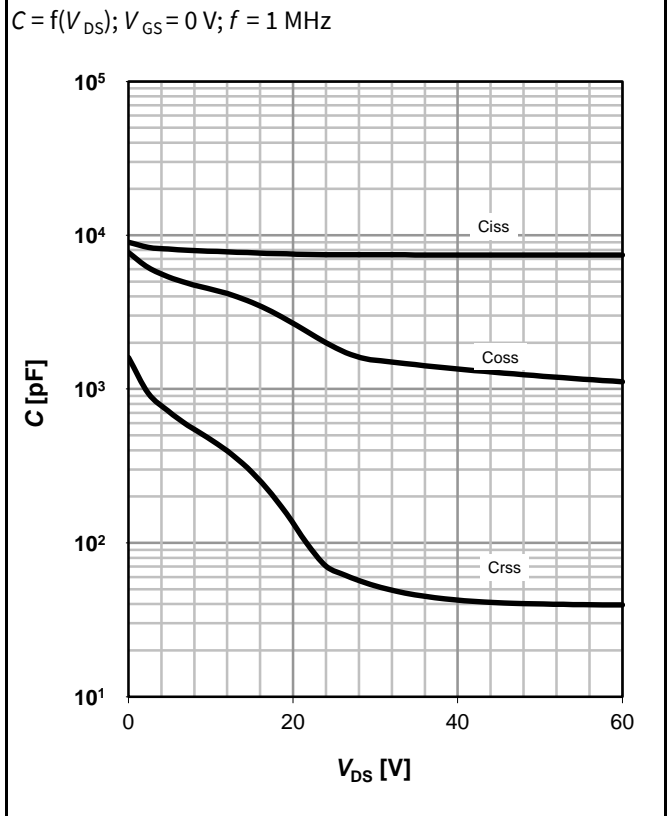
8 Typ. drain-source on-state resistance



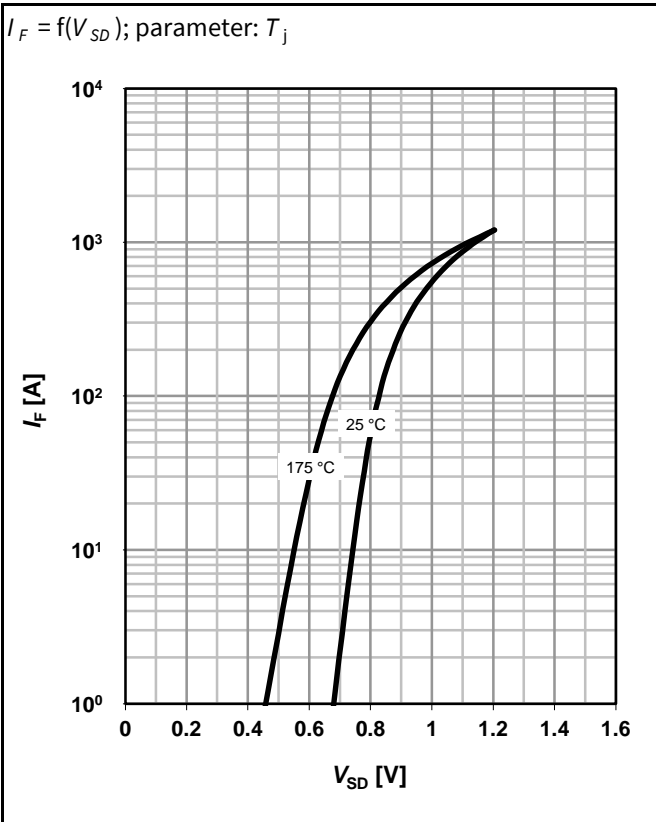
9 Typ. gate threshold voltage



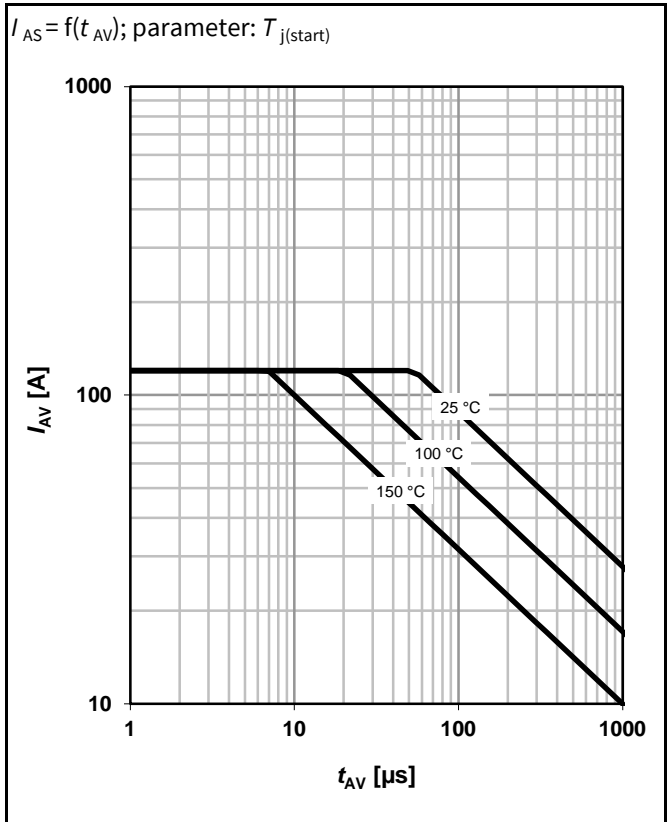
10 Typ. capacitances



11 Typical forward diode characteristics

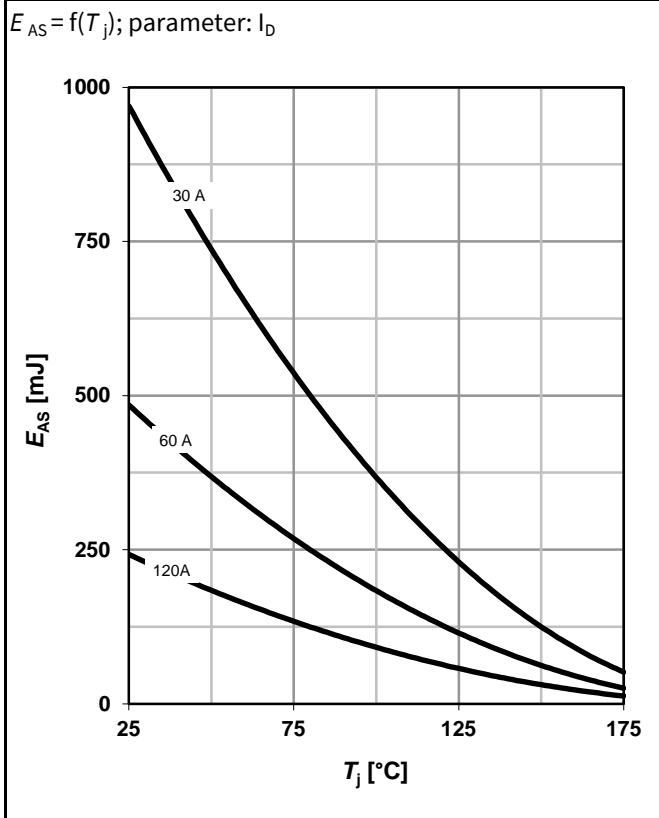


12 Typ. avalanche characteristics

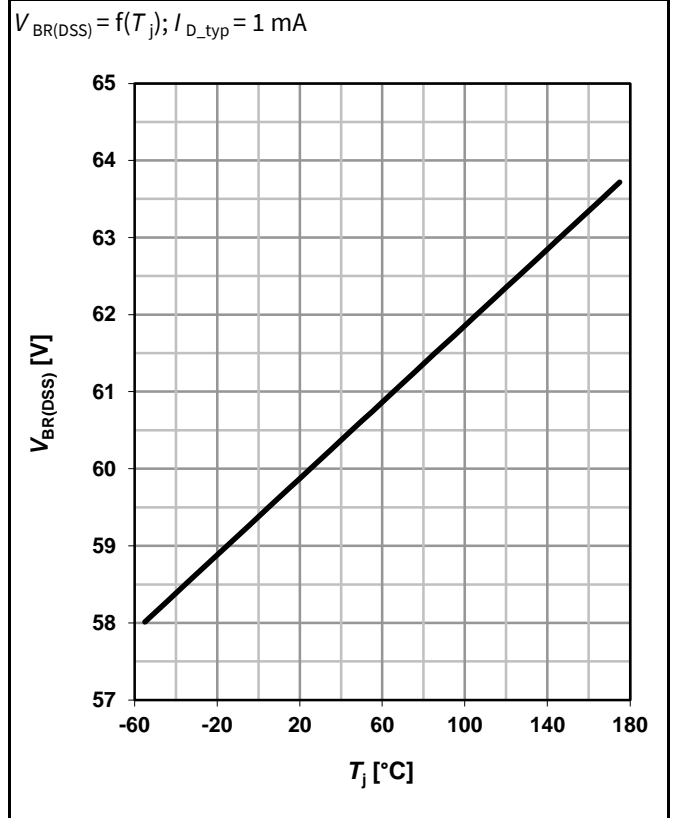




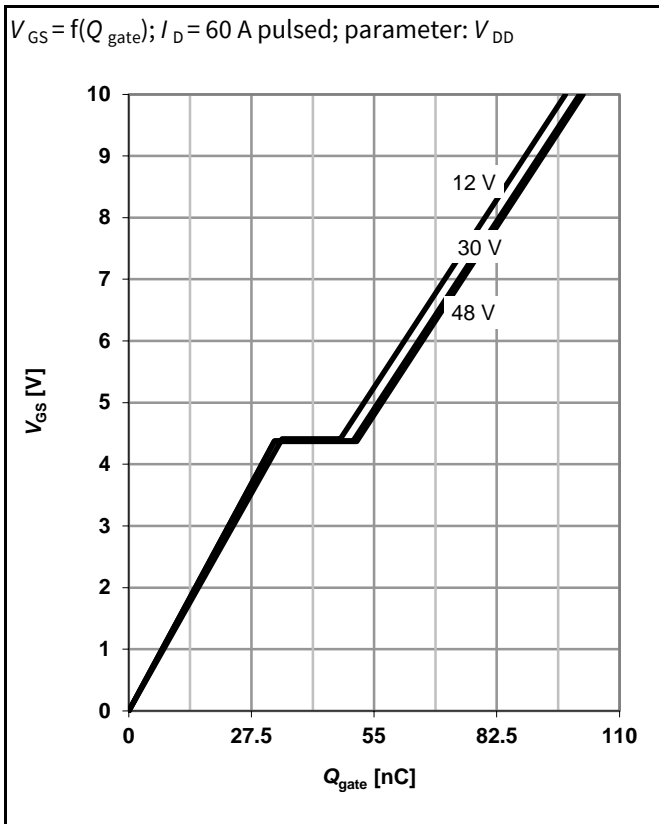
13 Typical avalanche energy



14 Drain-source breakdown voltage



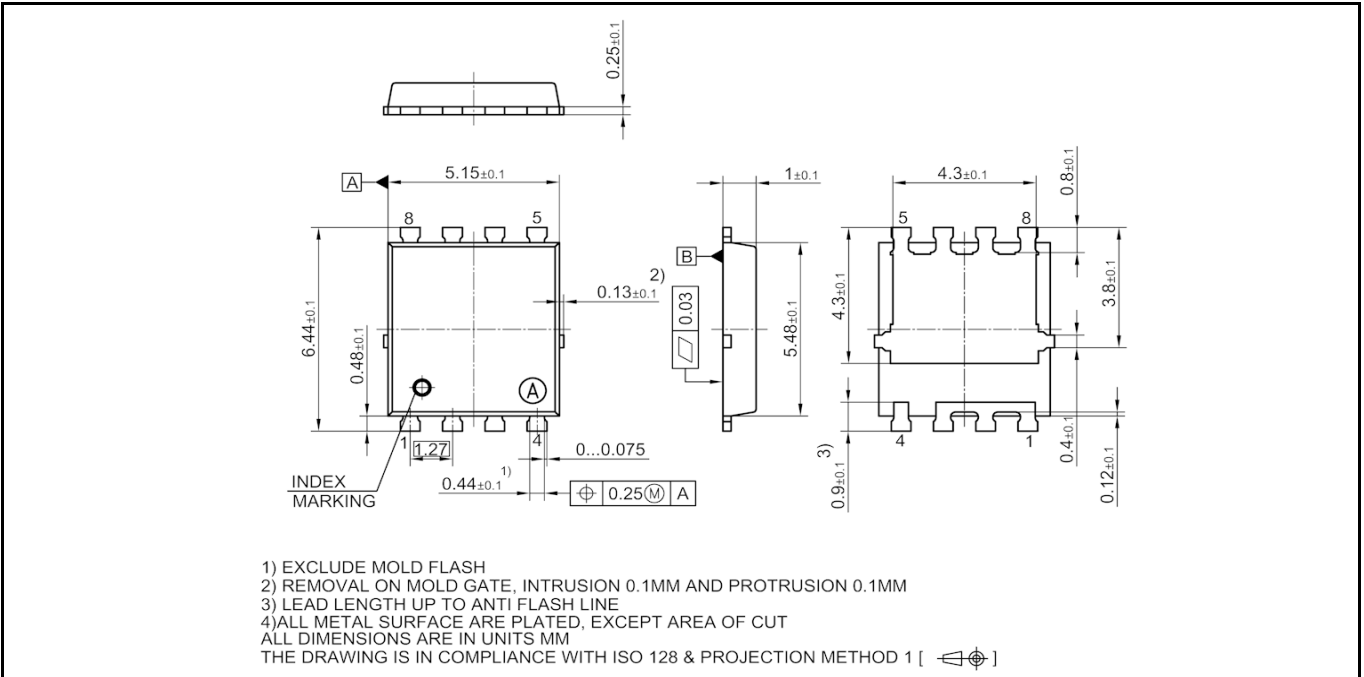
15 Typ. gate charge



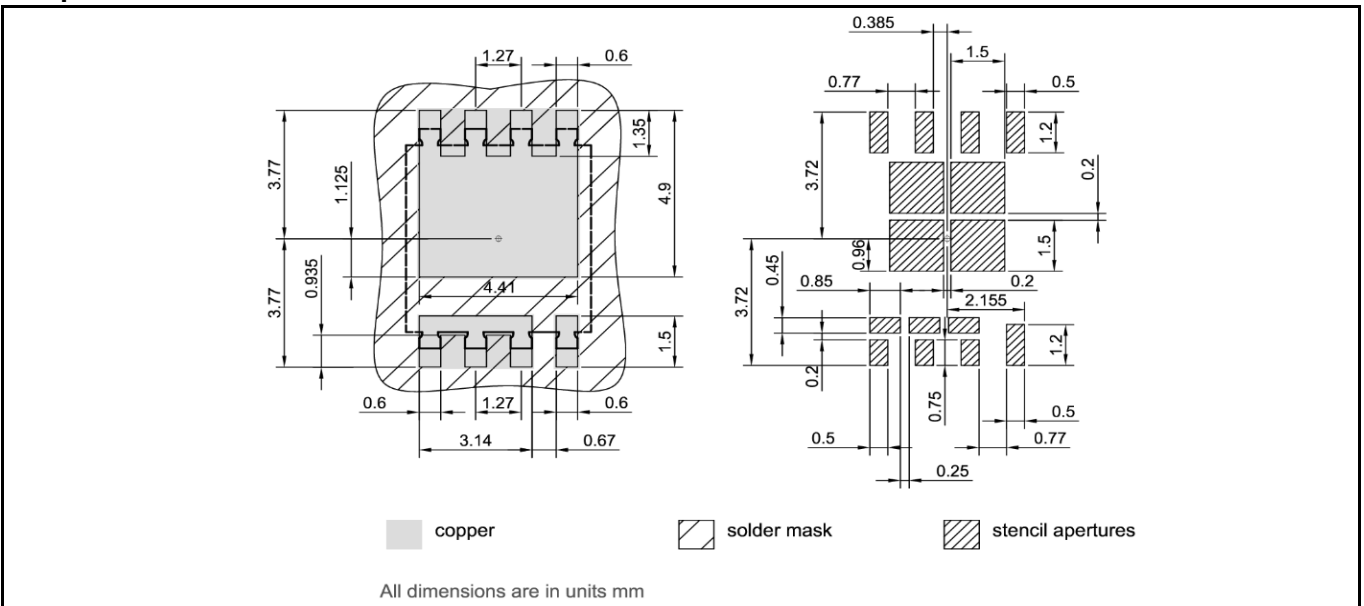
16 Gate charge waveforms



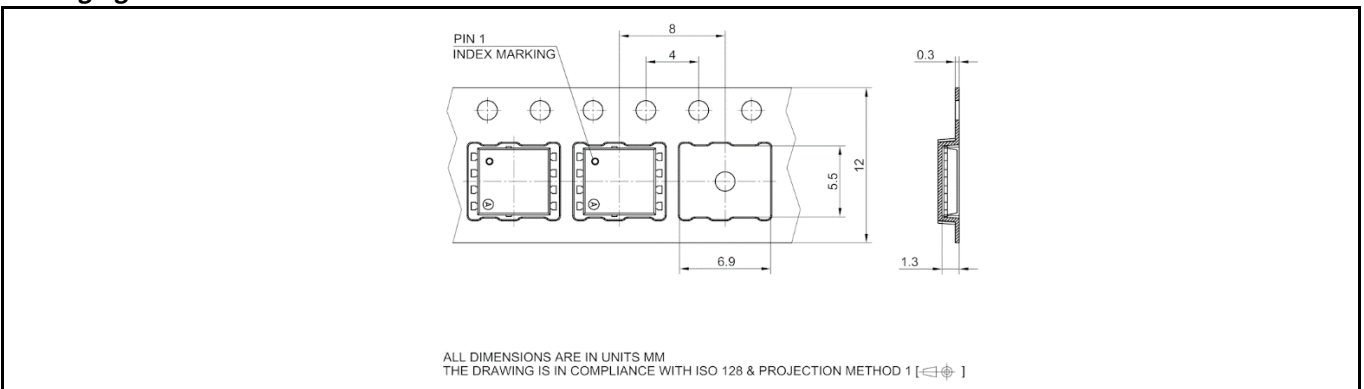
## Package Outline



## Footprint



## Packaging



**Revision History**

<b>Revision</b>	<b>Date</b>	<b>Changes</b>
Revision 1.0	04.02.2022	final data sheet
Revision 1.1	21.11.2022	dynamic characteristics on page 5

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